

**Texas A&M University
Department of Electrical and Computer Engineering**

ECEN 474/704 – (Analog) VLSI Circuit Design

Spring 2016

Exam #3

Instructor: Sam Palermo

- Please write your name in the space provided below
- Please verify that there are **5** pages (1 blank) in your exam
- You may use one double-sided page of notes and equations for the exam
- Good Luck!

Problem	Score	Max Score
1		35
2		35
3		30
Total		100

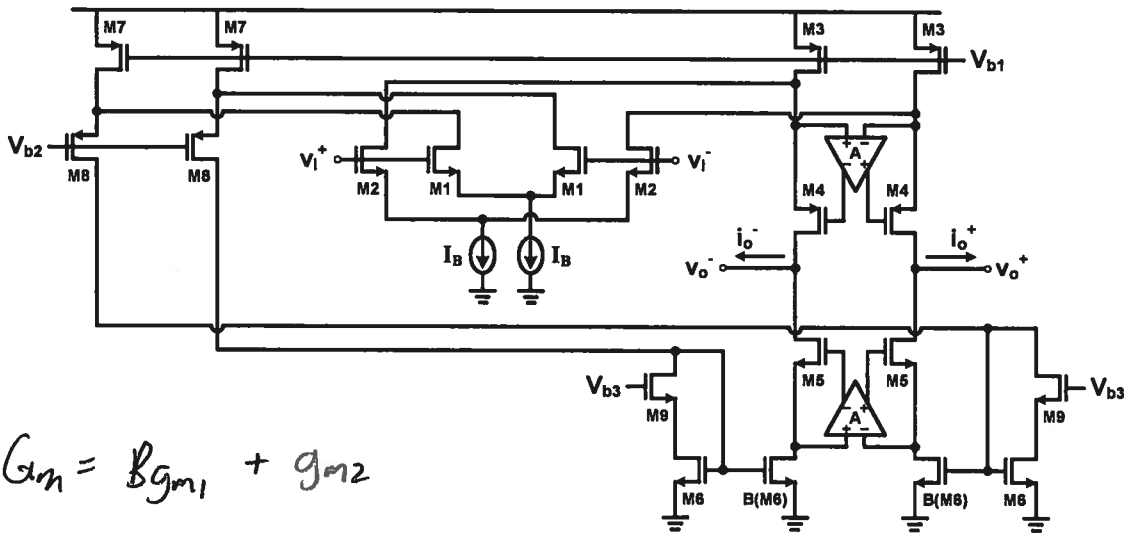
Name: SAM PALERMO

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Problem 1 (35 points)

For the fully-differential amplifier below, assume all transistors are operating in saturation, the internal amplifier blocks have finite gain A and infinite bandwidth. Note that the bottom-most nMOS transistors have a 1:B size ratio. Obtain expressions for the following:

- Small-signal differential transconductance, $(i_o^+ - i_o^-)/(v_i^+ - v_i^-)$.
- Output resistance.
- Fully differential amplifier DC gain, $A_{vd} = (v_o^+ - v_o^-)/(v_i^+ - v_i^-)$.
- Output referred noise current power spectral density. Consider only thermal noise and include all important noise sources.
- Input referred noise voltage power spectral density. Consider only thermal noise and include all important noise sources.



a. $G_m = Bg_{m1} + g_{m2}$

b. $R_{out} = \left[r_{o5} g_{m5} (1+A) \frac{r_{o6}}{B} \parallel r_{o4} g_{m4} (1+A) (r_{o3} \parallel r_{o2}) \right]$

c. $A_v = G_m R_{out} = \left[Bg_{m1} + g_{m2} \right] \left[r_{o5} g_{m5} (1+A) \frac{r_{o6}}{B} \parallel r_{o4} g_{m4} (1+A) (r_{o3} \parallel r_{o2}) \right]$

d. $\frac{i_{o,n}^2}{\Delta f} = (i_{o1}^2 + i_{o2}^2 + i_{o3}^2 + i_{o6}^2 + i_{o6M6}^2 + i_{o7}^2)^2$

$= \frac{16}{3} kT \left[B^2 g_{m1} + g_{m2} + g_{m3} + B^2 g_{m6} + Bg_{m6} + B^2 g_{m7} \right]$

e. $\frac{v_{i,n}^2}{\Delta f} = \frac{i_{o,n}^2}{\Delta f} \left(\frac{1}{G_m} \right)^2$

Problem 2 (35 points)

For the circuit shown below, assume that all transistors are operating in the saturation region **except for M9**. You can assume that the DC operating point for node B is the same as node A.

Calculate the following using these transistor parameters.

$$K_{PN} = \mu_n C_{ox} = 200 \mu A/V^2, V_{TH,N} = 0.4V, \lambda_N = 0.1V^{-1}$$

$$K_{PP} = \mu_p C_{ox} = 100 \mu A/V^2, V_{TH,P} = -0.4V, \lambda_P = 0.1V^{-1}$$

- Low-frequency gain ($A_{DC} = V_{out}/(V_i^+ - V_i^-)$)
- Dominant pole (ω_{p1})
- Second pole (ω_{p2})
- Unity-gain frequency (ω_{GX})
- Give the M9 aspect ratio 60° phase margin

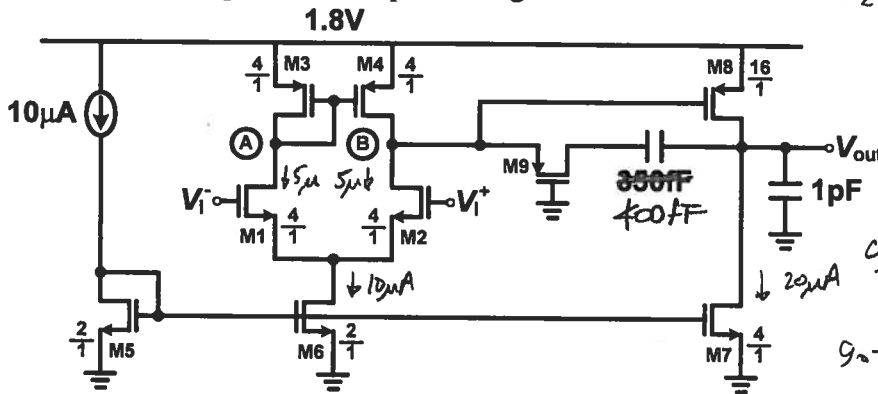
$$A_{DC} = \left(\frac{-g_{m2}}{g_{o2} + g_{o4}} \right) \left(\frac{-g_{m8}}{g_{o7} + g_{o8}} \right)$$

$$g_{m2} = \sqrt{(200) \left(\frac{4}{1} \right) (2)(5\mu)} = 89.4 \mu A/V$$

$$g_{o2} = g_{o4} = \lambda I_D = (0.1V^{-1})(5\mu A) = 0.5 \mu A/V$$

$$g_{m8} = \sqrt{(100) \left(\frac{16}{1} \right) (2)(20\mu)} = 253 \mu A/V$$

$$g_{o7} = g_{o8} = \lambda I_D = (0.1V^{-1})(20\mu A) = 2 \mu A/V$$



$$\text{Node } \textcircled{A} = \textcircled{B} = 1.8 - 0.4 - \sqrt{\frac{2(5\mu)}{100\mu(4)}} = 1.24V$$

$$A_{DC} = \left(\frac{89.4\mu}{0.5\mu + 0.5\mu} \right) \left(\frac{253\mu}{2\mu + 2\mu} \right) = 5.65 \times 10^3 V/V$$

$$\omega_{p1} = - \frac{(g_{o2} + g_{o4})(g_{o7} + g_{o8})}{g_{m8} C_c} = - \frac{(0.5\mu + 0.5\mu)(2\mu + 2\mu)}{(253\mu)(400fF)} = -39.5 \text{ krad/s} = -6.29 \text{ k}$$

$$\omega_{p2} = - \frac{g_{m8}}{C_L} = - \frac{253\mu}{1p} = -253 \text{ Mrad/s} = -40.3 \text{ MHz}$$

$$\omega_{GX} = A_{DC} \cdot |\omega_{p1}| = (5.65 \times 10^3)(39.5 \text{ k}) = 223 \text{ Mrad/s} = 35.5 \text{ MHz}$$

$$A_{DC} = 5.65 \times 10^3 V/V$$

$$\omega_{p1} = -39.5 \text{ krad/s}$$

$$\omega_{p2} = -253 \text{ Mrad/s}$$

$$\omega_{GX} = 223 \text{ Mrad/s}$$

$$PM = 180^\circ - \tan^{-1} \left(\frac{\omega_{GX}}{\omega_{p1}} \right) - \tan^{-1} \left(\frac{\omega_{GX}}{\omega_{p2}} \right) - \tan^{-1} \left(\frac{\omega_{GX}}{\omega_Z} \right)$$

$$60^\circ = 180^\circ - \tan^{-1} \left(\frac{223 \text{ M}}{39.5 \text{ k}} \right) - \tan^{-1} \left(\frac{223 \text{ M}}{253 \text{ M}} \right) - \tan^{-1} \left(\frac{223 \text{ M}}{\omega_Z} \right)$$

$$60^\circ = 180^\circ - 90^\circ - 41.4^\circ - \tan^{-1} \left(\frac{223 \text{ M}}{\omega_Z} \right)$$

$$(W/L)_9 \text{ for } PM=60^\circ = 1.92$$

$$11.4^\circ = -\tan^{-1} \left(\frac{223 \text{ M}}{\omega_Z} \right)$$

$$\omega_Z = - \frac{223 \text{ M}}{\tan(11.4^\circ)} = -1.11 \text{ Grad/s}$$

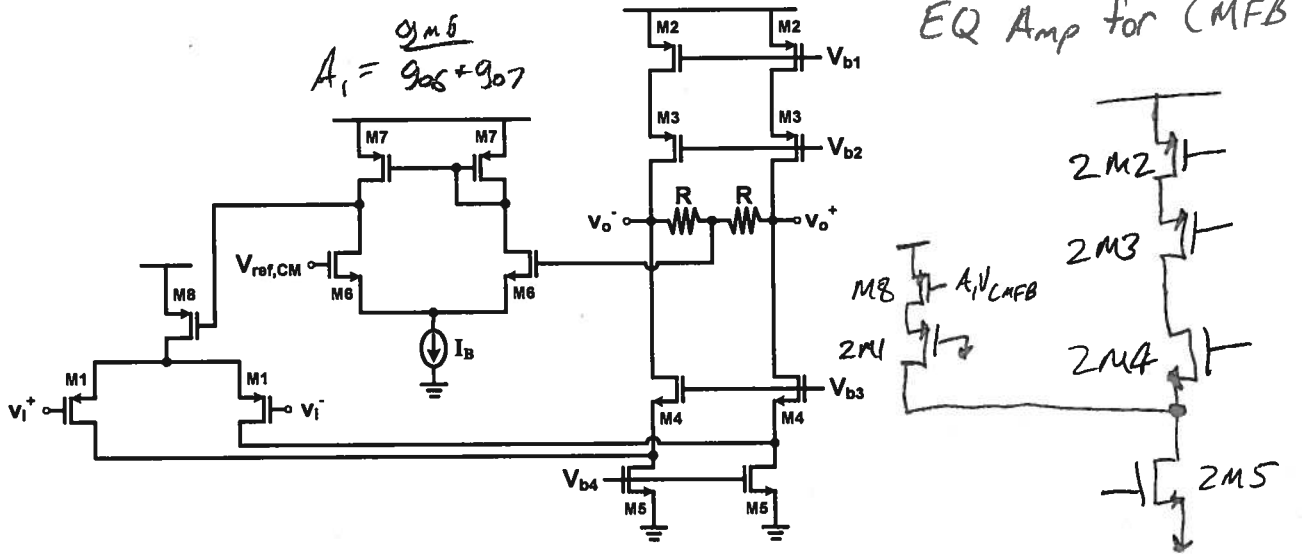
$$\omega_Z = \frac{1}{(g_{m8} - R_2)C_c} \quad \frac{\omega_Z}{L_9} = \frac{1}{(100\mu)(6.2k)(1.24 \text{ DA})}$$

$$R_2 = \frac{1}{g_{m8}} - \frac{1}{\omega_Z C_c} = 6.2k$$

Problem 3 (30 points)

For the fully differential amplifier with common-mode feedback (CMFB) below, assume all transistors are operating in saturation, and obtain the following:

- a) Neglecting the CMFB network, give an expression for the fully differential amplifier DC gain, $A_{vd} = (v_{o+} - v_{o-}) / (v_i^+ - v_i^-)$.
- b) Give an expression for the CMFB loop DC gain.



a. $A_{dd} = g_{m1} \left[g_{m4} r_{o4} (r_{o5} \parallel r_{o1}) \parallel g_{m3} r_{o3} r_{o2} \right]$

b. CMFB Loop Gain = $\left(\frac{g_{m6}}{g_{m6} + g_{m7}} \right) (-g_{m8}) \left[(2g_{m4}) \left(\frac{r_{o4}}{2} \right) \left[\frac{r_{o5}}{2} \parallel (2g_{m1}) \left(\frac{r_{o1}}{2} \right) r_{o3} \right] \parallel \left[(2g_{m3}) \left(\frac{r_{o3}}{2} \right) \left(\frac{r_{o2}}{2} \right) \right] \right]$

$\approx \left(-\frac{g_{m6} g_{m8}}{g_{m6} + g_{m7}} \right) \left(\frac{g_{m4} r_{o4} r_{o5}}{2} \parallel \frac{g_{m3} r_{o3} r_{o2}}{2} \right)$

Scratch Paper